## A fast guide to density functional calculations

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- I. From the many-particle problem to the Kohn-Sham functional
- II. How to perform a total energy calculation
- III. From the total energy to materials science

## General 'condensed-matter' Hamiltonian

$$(\hat{T}^e + \hat{T}^{ion} + \hat{V}^{e-e} + \hat{V}^{e-ion} + \hat{V}^{ion-ion})\Psi = E\Psi$$

wavefunction  $\Psi(\mathbf{r_1}, \cdots \mathbf{r_N}; \mathbf{R_I}, \cdots \mathbf{R_M})$ 

electronic coordinates  $\mathbf{r_k}$ ,  $k=1,\cdots N$ 

ionic coordintes  $\mathbf{R_I}$ ,  $I=1,\cdots M$ 

$$\hat{T}^e = \sum_{k=1}^N \frac{\mathbf{p}_k^2}{2m}$$

$$\hat{T}^{ion} = \sum_{I=1}^{M} \frac{\mathbf{P}_I^2}{2M_I}$$

$$\hat{V}^{e-e} = \frac{1}{4\pi\epsilon_0} \sum_{k \neq k'}^{N,N} \frac{e^2}{|\mathbf{r_k} - \mathbf{r_{k'}}|}$$

$$\hat{V}^{ion-ion} = \frac{1}{4\pi\epsilon_0} \sum_{I \neq I'}^{M,M} \frac{Z_I Z_{I'}}{|\mathbf{R_I} - \mathbf{R_{I'}}|}$$

$$\hat{V}^{e-ion}(\mathbf{r_k},\mathbf{R_I}) = \sum_{\mathbf{k}=1}^{N} \sum_{\mathbf{I}=1}^{M} \mathbf{v_I^{ion}}(|\mathbf{R_I} - \mathbf{r_k}|)$$

## **Born-Oppenheimer approximation**

separation of variables

parametric dependence on set of coord.  $\{\mathbf{R_I}\}$ 

$$\Psi(\mathbf{r_1}, \cdots \mathbf{r_N}; \mathbf{R_1}, \cdots \mathbf{R_M}) = \sum_{\nu} \Lambda_{\nu}(\{\mathbf{R_I}\}) \Phi_{\nu, \{\mathbf{R_I}\}}(\mathbf{r_k})$$

electronic Schrödinger equation

$$H_{\{\mathbf{R_{I}}\}}^{e} \Phi_{\nu, \{\mathbf{R_{I}}\}}(\mathbf{r_{k}}) = E_{\nu, \{\mathbf{R_{I}}\}}^{e} \Phi_{\nu, \{\mathbf{R_{I}}\}}(\mathbf{r_{k}})$$

$$H^{e} = T^{e} + V^{e-e} + V^{e-ion}$$

is obtained if we neglect

- ullet non-adiabatic couplings (usually terms of order  $m/M_I)$
- ullet electron-phonon couplings  $\Lambda_{
  u}$  between different electronic states

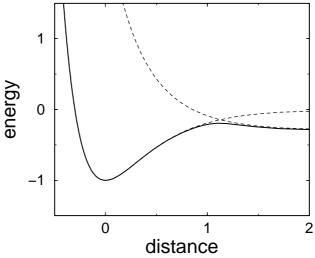
## Limitations of this approach

 doesn't account for correlated dynamics of ionic and electronic coordinates
 Example:

suprafluid He3, polaron-induced superconductivity

breakdown of the restriction to a single ground-state
 Born-Oppenheimer surface

Example: chemoluminescence



 breakdown of the adiabatic approximation Example:

excitation of surface plasmons during scattering of an ion from a metal surface

→ time-dependent theories (e.g. TD-DFT)

# electronic many-particle Hamiltonian

$$\left[\sum_{k=1}^{N} \frac{\nabla_k^2}{2m} + v^{(0)}(\mathbf{r_k}) + \sum_{k \neq k'}^{N,N} \frac{1}{2} W(\mathbf{r_k}, \mathbf{r_k'})\right] \Phi(\mathbf{r_1}, \dots \mathbf{r_N}) = E\Phi(\mathbf{r_1}, \dots \mathbf{r_N})$$

$$W(\mathbf{r}, \mathbf{r}') = \frac{e^2}{4\pi\epsilon_0 |\mathbf{r} - \mathbf{r}'|}$$

$$v^{(0)}(\mathbf{r}) = \sum_{I=1}^{M} v_I^{ion}(|\mathbf{R_I} - \mathbf{r}|)$$

still many (for a typical solid:  $10^{23}$ ) degrees of freedom

configuration interaction) molecules and clusters) using established methods of quantum chemistry (e.g. The many-particle problem can be solved only for rather small systems (atoms,

## **Density Functional Theory**

## Kohn-Hohenberg theorem:

For a given external potential  $v^{(0)}$ , the wavefunctions can be considered as functionals in the space of ground state densities, n:

$$E_{v^{(0)}}[n] = \langle \Phi[n] | \hat{T}^e + \frac{1}{2} \hat{W} + \hat{v}^{(0)} | \Phi[n] \rangle$$

The energy functional is stationary at the ground state energy, and the true ground state density  $n_0$  coincides with n at the stationary point. This allows for the definition of a universal functional  $\mathcal F$  with

$$E_{v^{(0)}}[n] = \mathcal{F}[n] + \int d\mathbf{r} \ v^{(0)}(\mathbf{r}) n(\mathbf{r})$$

### Kohn-Sham theorem:

$$\mathcal{F}[n] = T_0[n] + \frac{1}{2} \int \int d\mathbf{r} \, d\mathbf{r}' \, n(\mathbf{r}) W(\mathbf{r}, \mathbf{r}') n(\mathbf{r}') + E_{XC}[n]$$

 $T_0$ :

 $V_{XC}[n](r) := \frac{\delta E_{XC}[n]}{\delta n(r)}$ :

kinetic energy of a system of non-interacting particles exchange-correlation potential

## Kohn-Sham (single particle) Hamiltonian

To find the stationary point, we do variations at fixed  $N=\int d{\bf r}\, n({\bf r})$ , which leads to

$$\frac{\delta E_{v^{(0)}}}{\delta n(\mathbf{r})} = \mu$$
 (Lagrange parameter)

If we write the density as a sum over single-particle functions,

$$n(\mathbf{r}) = \sum_{j=1}^{N} \sum_{k \in BZ} |\varphi_{j,k}(\mathbf{r})|^{2},$$

the variational principle  $\delta E_{v^{(0)}}[\varphi^*]/\delta \varphi^*({\bf r})={\bf 0}$  leads to the Kohn-Sham equations

$$\left(-\frac{\nabla^2}{2m} + V_{\text{eff}}[n](\mathbf{r})\right)\varphi_{j,\mathbf{k}}(\mathbf{r}) = \epsilon_{j,\mathbf{k}}\varphi_{j,\mathbf{k}}(\mathbf{r})$$

with the effective potential

$$V_{\mathsf{eff}}[n](\mathbf{r}) = v_{R_I}^{(0)}(\mathbf{r}) + \int \!\! d\mathbf{r}' \frac{e^2 n(\mathbf{r}')}{4\pi\epsilon_0 |\mathbf{r} - \mathbf{r}'|} + \frac{\delta E_{XC}[n]}{\delta n}(\mathbf{r}).$$

# The total energy (for static ions)

$$E_{tot}[n] = T_0[n] + \int d\mathbf{r} \, v_{\mathbf{R}_i}^{(0)}(\mathbf{r}) n(\mathbf{r}) + \frac{1}{4\pi\epsilon_0} \int d\mathbf{r} \int d\mathbf{r}' \frac{e^2 n(\mathbf{r}) n(\mathbf{r}')}{2|\mathbf{r} - \mathbf{r}'|}$$

$$+ E_{XC}[n] + V_{\mathbf{R}_I}^{ion-ion}$$

$$E_{tot}[n] = \sum_{j=1}^{N} \sum_{\mathbf{k} \in \mathbf{BZ}} \varepsilon_{j,\mathbf{k}} + \Delta E^{e-e}[n] + \Delta E_{XC}[n] + V_{\mathbf{R}_I}^{ion-ion}$$

$$\Delta E^{e-e}[n] = -\frac{1}{4\pi\epsilon_0} \int d\mathbf{r} \int d\mathbf{r}' \frac{e^2 n(\mathbf{r}) n(\mathbf{r}')}{2|\mathbf{r} - \mathbf{r}'|} = -E^{e-e}[n]$$

$$\Delta E_{XC}[n] = E_{XC}[n] - \int d\mathbf{r} V_{XC}[n](\mathbf{r}) \mathbf{n}(\mathbf{r})$$

 $E_{tot}$  is stationary with resp. to variations of n around  $n_0$ , but the individual terms are not !

## How can we specify $E_{XC}$

At this point, we need to make approximations to get further. Example: local density approximation (LDA)

$$E_{XC}[n(\mathbf{r})] = \int d\mathbf{r} \ e_{XC}[n(\mathbf{r})] \ n(\mathbf{r})$$

$$\approx \int d\mathbf{r} \left[ e_X^{hom}(n(\mathbf{r})) + e_C^{hom}(n(\mathbf{r})) \right] n(\mathbf{r})$$

$$e_X^{hom}(n) = -(81/64\pi)^{1/3} n^{1/3} (\mathbf{r})$$

$$e_C^{hom}(n) = \begin{cases} -0.1423(1+1.0529\sqrt{r_s}+0.3334r_s)^{-1} & \text{if } r_s \ge 1, \\ -0.0480+0.0311 \ln r_s -0.0116r_s +0.002 & r_s & \ln r_s \\ & \text{if } r_s < 1. \end{cases}$$

 $r_s:=(4\pi n({f r})/{f 3})^{-1/3}$  Wigner-Seitz radius [see, e.g. Perdew & Zunger, PRB 23 5048 (1981)]

## Periodic systems

crystal structure =

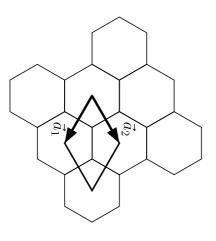
translational symmetry Bravais lattice

symmetries of the basis compatible with the Bravais lattice

group  $\mathcal T$ 

point group  ${\cal P}$ 

Example: twodimensional honeycomb lattice (Bravais lattice if a basis of two atoms is used)



lattice vectors  $\vec{a}_1$ ,  $\vec{a}_2$ ,  $\vec{a}_3$ 

• Brillouin zone (BZ)

reciprocal lattice vectors  $ar{b}_1$ ,  $ar{b}_2$ ,  $ar{b}_3$  $b_i = 2\pi/\Omega \left( \vec{a}_j \times \vec{a}_k \right)$ 

 $\{\{ijk\}=\{123\}$  & cyclic permutations of indices)

## **Bloch functions**

Since H commutes with the elements of  $\mathcal{T}$ , the wave functions must be of the form

$$\varphi_{i,\mathbf{k}}(\mathbf{r} + \mathbf{R}) = e^{i\mathbf{k}\mathbf{R}}\varphi_{i,\mathbf{k}}(\mathbf{r}),$$
 (Bloch's theorem)

for any  $\mathbf{R} = n_1 \vec{a}_1 + n_2 \vec{a}_2 + n_3 \vec{a}_3$ .

The wavevector  $\mathbf{k}$  is an index specified by a point in the first Brillouin zone (elementary cell of the reciprocal lattice), and the number of such points is equal to the number of lattice sites in the crystal.

Due to Bloch's theorem, it suffices to calculate  $\varphi$  in just one elementary cell,

$$\varphi_{j,\mathbf{k}}(\mathbf{r}) = e^{i\mathbf{k}\mathbf{r}} u_{j,\mathbf{k}}(\mathbf{r})$$

where u is a lattice-periodic function.

In practice, sums over k are evaluated by summing over a discrete set of (special) k-points.

## Basic steps in an electronic structure calculation

- guess a starting charge density
   (e.g. superposition of atomic densities)
- 2. set up the Hamiltonian for this charge density (usually done in a small, preliminary basis set)
- 3. diagonalize this approximative Hamiltonian
- 4. use the eigenvalues and wavefunctions to set up a new charge density
- 5. try to improve the wavefunctions using the variational principle for  $E_{tot}$ , thereby simultaneously approaching self-consistency

## Self-consistency cycle

## Harris functional

$$E_{tot}[n^{(i)}] = \sum_{j=1}^{N} \sum_{\mathbf{k} \in \mathrm{BZ}} \varepsilon_{j,\mathbf{k}} + \Delta E^{e-e}[n^{(i-1)}] + \Delta E_{XC}[n^{(i-1)}] + V_{\mathbf{R}_I}^{ion-ion}$$

update charge density

$$n^{(i)}(\mathbf{r}) = \sum_{\mathbf{k}}^{N_{\mathbf{k}}} \sum_{j}^{n_{B}} f_{j,\mathbf{k}} |arphi_{j,\mathbf{k}}^{(i)}(\mathbf{r})|^{2}$$
 with  $f_{i,j} = [\operatorname{con}(f_{i,j} - f_{i,j})/LT) - 1]-1$  in  $\mathbf{r}$ 

with  $f_{j,\mathbf{k}}=[\exp((\varepsilon_{j,\mathbf{k}}-\epsilon_F)/kT)-1]^{-1}$ . In principle, we are interested in  $T\to 0$ , but finite T helps to stabilize the SC loop.

$$\begin{split} \tilde{E}_{tot}[n^{(i+1)}] &= T_0[n^{(i)}] + \int d\mathbf{r} \, v_{\mathbf{R}_I}^{(0)}(\mathbf{r}) n^{(i)}(\mathbf{r}) \\ &+ E^{e-e}[n^{(i)}(\mathbf{r})] + E_{XC}[n^{(i)}] + V_{\mathbf{R}_I}^{ion-ion} \end{split}$$

Kohn-Sham functional:  $ilde{E}_{tot}[n_0] = E_{tot}[n_0]$  with self-consistent density  $n_0$ 

## Variational properties

At the stationary point, the Kohn-Sham equations lead us to

$$T_0[n] = \sum_{j=1}^{N} \sum_{\mathbf{k} \in BZ} \varepsilon_{j,\mathbf{k}} - \int d\mathbf{r} \, n(\mathbf{r}) V_{\mathsf{eff}}[n](\mathbf{r})$$

For the non-consistent case, we may introduce the generalization

$$T_0[n, V_{\text{eff}}] = \sum_{j=1}^{r} \sum_{\mathbf{k} \in \mathrm{BZ}} \varepsilon_{j,\mathbf{k}}[V_{\text{eff}}] - \int\! d\mathbf{r} \, n(\mathbf{r}) V_{\text{eff}}(\mathbf{r})$$

This can be used to define the 'double' functional

$$E_{tot}^{D}[n, V_{\mbox{eff}}] = T_0[n, V_{\mbox{eff}}] + E^{e-e}[n] + E_{XC}[n] + V_{\mbox{R}_I}^{ion-ion}$$

with the variational properties

$$E_{tot}^{D}[n_0 + \delta n, V_{\text{eff}}[n_0]] - E_{tot}^{D}[n_0, V_{\text{eff}}[n_0]] = c_1(\delta n)^2$$
  

$$E_{tot}^{D}[n_0, V_{\text{eff}}[n_0] + \delta v] - E_{tot}^{D}[n_0, V_{\text{eff}}[n_0]] = c_2(\delta v)^2$$

Normally, one has  $c_1>0,c_2<0$ . The Harris functional, in this notation, is  $E^D_{tot}[n^{(i-1)},V_{\mbox{eff}}[n^{(i-1)}]].$ 

## Total energy calculations and thermodynamics

The thermodynamic ground state is determined by the free energy of the system (for fixed volume)

$$F(T,V) = E_{tot}(T,V) - TS^{e}(T,V) + E_{kin}^{ion}(T) - TS^{ion}(T,V)$$

Structural relaxation:

Minimize F(T, V) (or  $E_{tot}$ , respectively)

**Caution:** ionic contribution to the free energy, important if, e.g., anharmonic effects come into play

or by the Gibbs free energy (for fixed pressure)

$$G(T, p) = F(T, V) + pV$$

### Examples:

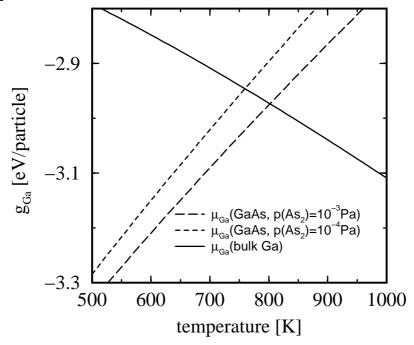
- equilibrium between two structural phases
- equilibrium between a solid and its vapor

## **Example: Thermal decay of GaAs**

$$GaAs \leftrightarrow Ga_{metal} + \frac{1}{2}As_2$$

$$G_{\text{Ga}}^{\text{GaAs bulk}}(p,T) = G_{\text{GaAs}}(T) - G_{\text{As}}(p,T).$$

 $G_{\rm As}(p,T)$  from ideal two-atomic gas,  $S_{\rm GaAs}^{ion}$  and  $S_{\rm Ga}^{ion}$  from Debye model of the solid.



Free enthalpy per Ga atom in bulk GaAs in thermodynamic equilibrium with  $As_2$  vapor at two pressures, compared to the free enthalpy per Ga atom in elemental Ga.

[P. Kratzer et al., Phys. Rev. B **59**, 15246 (1999)]

## Finite electronic temperature

occupation numbers from Fermi distribution  $f_{j,\mathbf{k}} = [\exp((\varepsilon_{j,\mathbf{k}} - \epsilon_F)/kT) - 1]^{-1}$   $\rightarrow$  The program actually computes the free energy F! entropy of the electronic system

$$S^{e} = 2k_{B} \sum_{j=1}^{n_{B}} \sum_{\mathbf{k} \in BZ} [f_{j,\mathbf{k}} \ln f_{j,\mathbf{k}} + (1 - f_{j,\mathbf{k}}) \ln(1 - f_{j,\mathbf{k}})]$$

For a (free-electron-like) metal, we have

$$F(T) = E(T=0) - \frac{\gamma}{2}T^2 + O(T^3)$$

$$E(T) = E(T=0) + \frac{\gamma}{2}T^2 + O(T^3)$$

extrapolation to zero electronic temperature

$$E(T=0) \approx [F(T) + E(T)]/2 = E(T) - S^{e}T/2$$

[see M. J. Gillan, J. Phys. Cond. Mat. 1, 689 (1989)]

## How to compute observable quantities

## A) energy differences

between different structures, formation energy of defects, heat of adsorption, . . .

**B)** derivatives of the thermodynamic potentials  $E_{tot}$ , F or G

For simplicity's sake, we consider a system with constant volume at T=0:

$$F(T=0,V) = E_{tot}(V)$$

pressure 
$$p=-rac{\partial E_{tot}(V)}{\partial V}$$

bulk modulus  $B = V \frac{\partial^2 E_{tot}(V)}{\partial V^2}$ 

forces  $ec{F}_I$  on atom I (in electronic ground state)

$$\vec{F}_I = -\frac{\partial E_{tot}}{\partial \vec{R}_I} = \sum_{j}^{N} \langle \varphi_{j,\mathbf{k}} | \partial H / \partial \vec{R}_I | \varphi_{j,\mathbf{k}} \rangle$$

due to the Hellmann-Feynman theorem

## C) second derivatives

## Examples:

1 force constant matrix

$$\frac{\partial E_{tot}}{\partial \vec{R}_i \partial \vec{R}_j}$$

- ightarrow calculation of phonon spectrum, vibrational entropy, . . .
- 2. particle number fluctuations
- → chemical softness and hardness

$$s(\mathbf{r}) = \left(\frac{\partial n(\mathbf{r})}{\partial \mu}\right)\Big|_{v,T} = \int \left(\frac{\delta^2 E_{tot}}{\delta n(\mathbf{r})\delta n(\mathbf{r}')}\right)^{-1} d\mathbf{r}'$$

$$h(\mathbf{r}) = \frac{1}{2} \left( \frac{\partial \mu}{\partial n(\mathbf{r})} \right) \Big|_{v,T} = \int \frac{\delta^2 E_{tot}}{\delta n(\mathbf{r}) \delta n(\mathbf{r}')} \frac{n(\mathbf{r}')}{2N} d\mathbf{r}'$$

**Note:** When calculating second derivatives, the response of the density must be taken into account.

ightarrow Density Functional Perturbation Theory

## What materials properties are accessable to calculation?

structural properties

Examples: structural phase transitions, surface reconstructions

• elastic properties

Examples: bulk modulus,  $C_{11}$ ,  $C_{12}$ ,  $C_{44}$ , . . . yes

chemical properties

Examples: thermochemical stability of compounds, reactivity of surfaces yes

• transport properties

Examples: transport effective mass, magnetoresistence developing field

• optical/spectroscopic properties

Examples: photoemission spectra, cross sections for light absorption

topic beyond Kohn-Sham theory, encouraging progress recently

many other applications

## Transport theory based on first-principles

From the Kohn-Sham variational principle, we have

$$\frac{\delta E_{tot}}{\delta n(\mathbf{r})} = \mu = \epsilon_F \quad \text{in a metal}$$

However, there is no strict proof that the Fermi surface is represented correctly in DFT. Further, in a Kohn-Sham theory,  $\epsilon_{j,\mathbf{k}}$  cannot be identified with the excitation energy of quasiparticles or quasiholes. One can only show

$$\frac{\partial E_{tot}}{\partial f_{j,\mathbf{k}}} = \epsilon_{j,\mathbf{k}}.$$

[supposing that  $E_{XC}$  is a continuously differentiable function of particle number]

Still one may use

$$\left(\frac{\partial \epsilon_{j,\mathbf{k}}}{\partial k_n \partial k_m}\right)\Big|_{\epsilon=\epsilon_F} = (\mathbf{M}^{-1})_{nm}$$

as an approximation to the effective mass tensor.

The transport cross section for impurity scattering can be calculated from the 'golden rule' expression,

$$d\sigma(\hat{\mathbf{k}}, \hat{\mathbf{k}}') = 2\pi/\hbar (1 - \hat{\mathbf{k}}\hat{\mathbf{k}}') |V_{\mathbf{k},\mathbf{k}'}|^2 \rho(\epsilon_{\mathbf{k}'}) d\hat{\mathbf{k}}',$$

using  $\rho$ , the density of states at the Fermi energy, from a DFT calculation as input.

## **Simulation techniques**

In many materials science problems length scales much larger than the atomic scale are involved (e.g. in phase transitions, line defects, plastic deformation, etc.). Further, one is interested in dynamic (rather than static) properties, and evolution on time scales as long as seconds.

These problems require simulation techniques which build upon the reliability of the first-principles approach, but extend its range of applicability.

## molecular dynamics

- to follow dynamical processes in time, e.g. chemical reactions scale: several hundred atoms, pico-seconds
- for calculation of vibrational properties & phonons (Fourier transform of time correlation functions)
- as a way to calculate the free energy at finite T (performing a time average)

## statistical physics

statistical treatment of a discrete Hamiltonian with parameters taken from DFT calculations

### kinetics

description of 'rare' events using rate laws